

Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

E·XF

Product Status	Active
Core Processor	PIC
Core Size	8-Bit
Speed	40MHz
Connectivity	UART/USART
Peripherals	Brown-out Detect/Reset, LVD, POR, PWM, WDT
Number of I/O	16
Program Memory Size	8KB (4K × 16)
Program Memory Type	FLASH
EEPROM Size	256 x 8
RAM Size	256 x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 5.5V
Data Converters	A/D 7x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	28-VQFN Exposed Pad
Supplier Device Package	28-QFN (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic18lf1320t-i-ml

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

TO OUR VALUED CUSTOMERS

It is our intention to provide our valued customers with the best documentation possible to ensure successful use of your Microchip products. To this end, we will continue to improve our publications to better suit your needs. Our publications will be refined and enhanced as new volumes and updates are introduced.

If you have any questions or comments regarding this publication, please contact the Marketing Communications Department via E-mail at **docerrors@microchip.com**. We welcome your feedback.

Most Current Data Sheet

To obtain the most up-to-date version of this data sheet, please register at our Worldwide Web site at:

http://www.microchip.com

You can determine the version of a data sheet by examining its literature number found on the bottom outside corner of any page. The last character of the literature number is the version number, (e.g., DS3000000A is version A of document DS30000000).

Errata

An errata sheet, describing minor operational differences from the data sheet and recommended workarounds, may exist for current devices. As device/documentation issues become known to us, we will publish an errata sheet. The errata will specify the revision of silicon and revision of document to which it applies.

To determine if an errata sheet exists for a particular device, please check with one of the following:

- Microchip's Worldwide Web site; http://www.microchip.com
- Your local Microchip sales office (see last page)

When contacting a sales office, please specify which device, revision of silicon and data sheet (include literature number) you are using.

Customer Notification System

Register on our web site at www.microchip.com to receive the most current information on all of our products.

U-0	U-0	R/W-0/0	R/W-0/0	R/W-0/0	R/W-0/0	R/W-0/0	R/W-0/0		
_	—			TUN	<5:0>				
bit 7							bit 0		
Legend:									
R = Readab	le bit	W = Writable	V = Writable bit U = Unimplemented bit, read as '0'						
u = Bit is un	changed	x = Bit is unkr	nown	-n/n = Value at POR and BOR/Value at all other Res					
'1' = Bit is set '0' = Bit is cleared									
bit 7-6	Unimpleme	nted: Read as '	0'						
bit 5-0	TUN<5:0>:	Frequency Tunir	ng bits						
	100000 = N	/linimum frequer	псу						
	•								
	•								
	111111 =								
	000000 = 0	Dscillator module	e is running at	the factory-calil	brated frequen	су			
	000001 =								
	•								
	•								
	• 011110 =								
	011111 = 1								

REGISTER 2-1: OSCTUNE: OSCILLATOR TUNING REGISTER

2.7 Clock Sources and Oscillator Switching

Like previous PIC18 devices, the PIC18F1220/1320 devices include a feature that allows the system clock source to be switched from the main oscillator to an alternate low-frequency clock source. PIC18F1220/1320 devices offer two alternate clock sources. When enabled, these give additional options for switching to the various power managed operating modes.

Essentially, there are three clock sources for these devices:

- · Primary oscillators
- Secondary oscillators
- Internal oscillator block

The **primary oscillators** include the External Crystal and Resonator modes, the External RC modes, the External Clock modes and the internal oscillator block. The particular mode is defined on POR by the contents of Configuration Register 1H. The details of these modes are covered earlier in this chapter.

The **secondary oscillators** are those external sources not connected to the OSC1 or OSC2 pins. These sources may continue to operate even after the controller is placed in a power managed mode. PIC18F1220/1320 devices offer only the Timer1 oscillator as a secondary oscillator. This oscillator, in all power managed modes, is often the time base for functions such as a real-time clock.

Most often, a 32.768 kHz watch crystal is connected between the RB6/T1OSO and RB7/T1OSI pins. Like the LP mode oscillator circuit, loading capacitors are also connected from each pin to ground. These pins are also used during ICSP operations.

The Timer1 oscillator is discussed in greater detail in **Section 12.2 "Timer1 Oscillator**".

In addition to being a primary clock source, the **internal oscillator block** is available as a power managed mode clock source. The INTRC source is also used as the clock source for several special features, such as the WDT and Fail-Safe Clock Monitor.

The clock sources for the PIC18F1220/1320 devices are shown in Figure 2-8. See **Section 12.0 "Timer1 Module**" for further details of the Timer1 oscillator. See **Section 19.1 "Configuration Bits**" for Configuration register details.

5.0 MEMORY ORGANIZATION

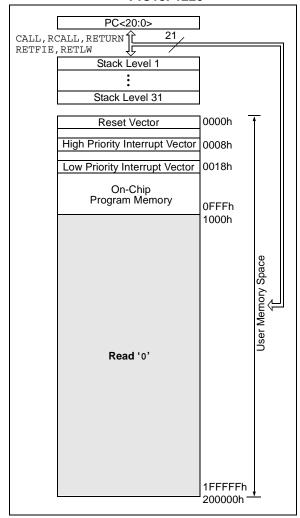
There are three memory types in Enhanced MCU devices. These memory types are:

- Program Memory
- Data RAM
- Data EEPROM

Data and program memory use separate busses, which allows for concurrent access of these types.

Additional detailed information for Flash program memory and data EEPROM is provided in Section 6.0 "Flash Program Memory" and Section 7.0 "Data **EEPROM Memory**", respectively.

FIGURE 5-1: PROGRAM MEMORY MAP AND STACK FOR PIC18F1220



5.1 **Program Memory Organization**

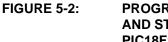
A 21-bit program counter is capable of addressing the 2-Mbyte program memory space. Accessing a location between the physically implemented memory and the 2-Mbyte address will cause a read of all '0's (a NOP instruction).

The PIC18F1220 has 4 Kbytes of Flash memory and can store up to 2,048 single-word instructions.

The PIC18F1320 has 8 Kbytes of Flash memory and can store up to 4,096 single-word instructions.

The Reset vector address is at 0000h and the interrupt vector addresses are at 0008h and 0018h.

The program memory maps for the PIC18F1220 and PIC18F1320 devices are shown in Figure 5-1 and Figure 5-2, respectively.



PROGRAM MEMORY MAP AND STACK FOR PIC18F1320

	PC<20:0>		
CALL, RORE	CALL, RETURN 21		
	Stack Level 1		
	•••		
	Stack Level 31		
	Reset Vector	0000h	
	High Priority Interrupt Vector	0008h	
	Low Priority Interrupt Vector	0018h	
	On-Chip Program Memory	1FFFh	
	Read '0'	2000h	User Memory Space
		1FFFFFh 200000h	<u>,</u>

5.12 Indirect Addressing, INDF and FSR Registers

Indirect addressing is a mode of addressing data memory, where the data memory address in the instruction is not fixed. An FSR register is used as a pointer to the data memory location that is to be read or written. Since this pointer is in RAM, the contents can be modified by the program. This can be useful for data tables in the data memory and for software stacks. Figure 5-8 shows how the fetched instruction is modified prior to being executed.

Indirect addressing is possible by using one of the INDF registers. Any instruction, using the INDF register, actually accesses the register pointed to by the File Select Register, FSR. Reading the INDF register itself, indirectly (FSR = 0), will read 00h. Writing to the INDF register indirectly, results in a no operation (NOP). The FSR register contains a 12-bit address, which is shown in Figure 5-9.

The INDFn register is not a physical register. Addressing INDFn actually addresses the register whose address is contained in the FSRn register (FSRn is a pointer). This is indirect addressing.

Example 5-5 shows a simple use of indirect addressing to clear the RAM in Bank 1 (locations 100h-1FFh) in a minimum number of instructions.

EXAMPLE 5-5: HOW TO CLEAR RAM (BANK 1) USING INDIRECT ADDRESSING

	LFSR	FSR0,0x100	;	
NEXT	CLRF	POSTINC0	;	Clear INDF
			;	register then
			;	inc pointer
	BTFSS	FSROH, 1	;	All done with
			;	Bank1?
	GOTO	NEXT	;	NO, clear next
CONTIN	UE		;	YES, continue

There are three indirect addressing registers. To address the entire data memory space (4096 bytes), these registers are 12-bit wide. To store the 12 bits of addressing information, two 8-bit registers are required:

- 1. FSR0: composed of FSR0H:FSR0L
- 2. FSR1: composed of FSR1H:FSR1L
- 3. FSR2: composed of FSR2H:FSR2L

In addition, there are registers INDF0, INDF1 and INDF2, which are not physically implemented. Reading or writing to these registers activates indirect addressing, with the value in the corresponding FSR register being the address of the data. If an instruction writes a value to INDF0, the value will be written to the address pointed to by FSR0H:FSR0L. A read from INDF1 reads the data from the address pointed to by FSR1H:FSR1L. INDFn can be used in code anywhere an operand can be used.

If INDF0, INDF1 or INDF2 are read indirectly via an FSR, all '0's are read (zero bit is set). Similarly, if INDF0, INDF1 or INDF2 are written to indirectly, the operation will be equivalent to a NOP instruction and the Status bits are not affected.

5.12.1 INDIRECT ADDRESSING OPERATION

Each FSR register has an INDF register associated with it, plus four additional register addresses. Performing an operation using one of these five registers determines how the FSR will be modified during indirect addressing.

When data access is performed using one of the five INDFn locations, the address selected will configure the FSRn register to:

- Do nothing to FSRn after an indirect access (no change) INDFn
- Auto-decrement FSRn after an indirect access (post-decrement) POSTDECn
- Auto-increment FSRn after an indirect access (post-increment) POSTINCn
- Auto-increment FSRn before an indirect access (pre-increment) PREINCn
- Use the value in the WREG register as an offset to FSRn. Do not modify the value of the WREG or the FSRn register after an indirect access (no change) – PLUSWn

When using the auto-increment or auto-decrement features, the effect on the FSR is not reflected in the Status register. For example, if the indirect address causes the FSR to equal '0', the Z bit will not be set.

Auto-incrementing or auto-decrementing an FSR affects all 12 bits. That is, when FSRnL overflows from an increment, FSRnH will be incremented automatically.

Adding these features allows the FSRn to be used as a stack pointer, in addition to its uses for table operations in data memory.

Each FSR has an address associated with it that performs an indexed indirect access. When a data access to this INDFn location (PLUSWn) occurs, the FSRn is configured to add the signed value in the WREG register and the value in FSR to form the address before an indirect access. The FSR value is not changed. The WREG offset range is -128 to +127.

If an FSR register contains a value that points to one of the INDFn, an indirect read will read 00h (zero bit is set), while an indirect write will be equivalent to a NOP (Status bits are not affected).

If an indirect addressing write is performed when the target address is an FSRnH or FSRnL register, the data is written to the FSR register, but no pre- or post-increment/ decrement is performed.

EXAMPLE 6-3: WRITING TO FLASH PROGRAM MEMORY (CONTINUED)

WRITE_WORD	_TO_HREG	S			
	MOVF	POSTINC	0, W	;	get low byte of buffer data and increment FSR0
	MOVWF	TABLAT		;	present data to table latch
	TBLWT+*	:		;	short write
				;	to internal TBLWT holding register, increment TBLPTR
	DECFSZ	COUNTER		;	loop until buffers are full
	GOTO	WRITE_W	ORD_TO_HREGS		
PROGRAM_MEI	MORY				
	BCF	INTCON,	GIE	;	disable interrupts
	MOVLW	55h		;	required sequence
	MOVWF	EECON2		;	write 55H
	MOVLW	AAh			
	MOVWF	EECON2		;	write AAH
	BSF	EECON1,	WR	;	start program (CPU stall)
	NOP				
	BSF	INTCON,	GIE	;	re-enable interrupts
	DECFSZ	COUNTER	_HI	;	loop until done
	GOTO PF	ROGRAM_LC	OOP		
	BCF	EECON1,	WREN	;	disable write to memory

6.5.2 WRITE VERIFY

Depending on the application, good programming practice may dictate that the value written to the memory should be verified against the original value. This should be used in applications where excessive writes can stress bits near the specification limit.

6.5.3 UNEXPECTED TERMINATION OF WRITE OPERATION

If a write is terminated by an unplanned event, such as loss of power or an unexpected Reset, the memory location just programmed should be verified and reprogrammed if needed. The WRERR bit is set when a write operation is interrupted by a MCLR Reset, or a WDT Time-out Reset during normal operation. In these situations, users can check the WRERR bit and rewrite the location.

6.6 Flash Program Operation During Code Protection

See **Section 19.0 "Special Features of the CPU"** for details on code protection of Flash program memory.

	BLE 0-2. REGISTERS ASSOCIATED WITH PROGRAM PLASH MEMORI													
Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Value on: POR, BOR	Value on all other Resets				
TBLPTRU	_		bit 21	Program M	rogram Memory Table Pointer Upper Byte (TBLPTR<20:16>)00 000000 000									
TBPLTRH	Program N	Program Memory Table Pointer High Byte (TBLPTR<15:8>) 0000 0000												
TBLPTRL	Program Memory Table Pointer High Byte (TBLPTR<7:0>) 0000 000													
TABLAT	Program N	lemory Table	e Latch						0000 0000	0000 0000				
INTCON	GIE/GIEH	PEIE/GIEL	TMR0IE	INTE	RBIE	TMR0IF	INTF	RBIF	0000 000x	0000 000u				
EECON2	EEPROM	Control Regi	ster 2 (no	t a physical	l register)					—				
EECON1	EEPGD	CFGS	_	FREE	WRERR	WREN	WR	RD	xx-0 x000	uu-0 u000				
IPR2	OSCFIP	_	_	EEIP	_	LVDIP	TMR3IP	_	11 -11-	11 -11-				
PIR2	OSCFIF		_	EEIF	_	LVDIF	TMR3IF		00 -00-	00 -00-				
PIE2	OSCFIE		_	EEIE	_	LVDIE	TMR3IE		00 -00-	00 -00-				

TABLE 6-2: REGISTERS ASSOCIATED WITH PROGRAM FLASH MEMORY

IADLL	10-5.											
		SYNC = 0, BRGH = 1, BRG16 = 1 or SYNC = 1, BRG16 = 1										
BAUD	Fosc	= 40.000) MHz	Fosc	= 20.00	0 MHz	Fosc	= 10.000) MHz	Fosc = 8.000 MHz		
RATE (K)	Actual Rate (K)	% Error	SPBRG value (decimal)	Actual Rate (K)	% Error	SPBRG value (decimal)	Actual Rate (K)	% Error	SPBRG value (decimal)	Actual Rate (K)	% Error	SPBRG value (decimal)
0.3	0.300	0.00	33332	0.300	0.00	16665	0.300	0.00	8332	300	-0.01	6665
1.2	1.200	0.00	8332	1.200	0.02	4165	1.200	0.02	2082	1200	-0.04	1665
2.4	2.400	0.02	4165	2.400	0.02	2082	2.402	0.06	1040	2400	-0.04	832
9.6	9.606	0.06	1040	9.596	-0.03	520	9.615	0.16	259	9615	-0.16	207
19.2	19.193	-0.03	520	19.231	0.16	259	19.231	0.16	129	19230	-0.16	103
57.6	57.803	0.35	172	57.471	-0.22	86	58.140	0.94	42	57142	0.79	34
115.2	114.943	-0.22	86	116.279	0.94	42	113.636	-1.36	21	117647	-2.12	16
		SYN	IC = 0, BR(GH = 1, BF	RG16 = 1	or SYNC =	1, BRG1	6 = 1				
BAUD	Fos	c = 4.000	MHz	Fost	c = 2.000	MHz	Fos	c = 1.000	MHz			
RATE (K)	Actual Rate (K)	% Error	SPBRG value (decimal)	Actual Rate (K)	% Error	SPBRG value (decimal)	Actual Rate (K)	% Error	SPBRG value (decimal)			
0.3	0.300	0.01	3332	300	-0.04	1665	300	-0.04	832			
1.2	1.200	0.04	832	1201	-0.16	415	1201	-0.16	207			

207

51

25

8

2403

9615

19230

_

_

-0.16

-0.16

-0.16

_

_

103

25

12

_

TABLE 16-3: **BAUD RATES FOR ASYNCHRONOUS MODES (CONTINUED)**

415

103

51

16

8

2403

9615

19230

55555

-0.16

-0.16

-0.16

3.55

_

2.4

9.6

19.2

57.6

115.2

2.404

9.615

19.231

58.824

111.111

0.16

0.16

0.16

2.12

-3.55

16.3.4 AUTO-WAKE-UP ON SYNC BREAK CHARACTER

During Sleep mode, all clocks to the EUSART are suspended. Because of this, the Baud Rate Generator is inactive and a proper byte reception cannot be performed. The auto-wake-up feature allows the controller to wake-up due to activity on the RX/DT line while the EUSART is operating in Asynchronous mode.

The auto-wake-up feature is enabled by setting the WUE bit (BAUDCTL<1>). Once set, the typical receive sequence on RX/DT is disabled and the EUSART remains in an Idle state, monitoring for a wake-up event independent of the CPU mode. A wake-up event consists of a high-to-low transition on the RX/DT line. (This coincides with the start of a Sync Break or a Wake-up Signal character for the LIN protocol.)

Following a wake-up event, the module generates an RCIF interrupt. The interrupt is generated synchronously to the Q clocks in normal operating modes (Figure 16-7) and asynchronously if the device is in Sleep mode (Figure 16-8). The interrupt condition is cleared by reading the RCREG register.

The WUE bit is automatically cleared once a low-to-high transition is observed on the RX line, following the wakeup event. At this point, the EUSART module is in Idle mode and returns to normal operation. This signals to the user that the Sync Break event is over.

16.3.4.1 Special Considerations Using Auto-Wake-up

Since auto-wake-up functions by sensing rising edge transitions on RX/DT, information with any state changes before the Stop bit may signal a false end-of-character

and cause data or framing errors. To work properly, therefore, the initial character in the transmission must be all '0's. This can be 00h (8 bytes) for standard RS-232 devices, or 000h (12 bits) for LIN bus.

Oscillator start-up time must also be considered, especially in applications using oscillators with longer start-up intervals (i.e., LP, XT or HS/PLL mode). The Sync Break (or Wake-up Signal) character must be of sufficient length and be followed by a sufficient period, to allow enough time for the selected oscillator to start and provide proper initialization of the EUSART.

16.3.4.2 Special Considerations Using the WUE Bit

The timing of WUE and RCIF events may cause some confusion when it comes to determining the validity of received data. As noted, setting the WUE bit places the EUSART in an Idle mode. The wake-up event causes a receive interrupt by setting the RCIF bit. The WUE bit is cleared after this when a rising edge is seen on RX/ DT. The interrupt condition is then cleared by reading the RCREG register. Ordinarily, the data in RCREG will be dummy data and should be discarded.

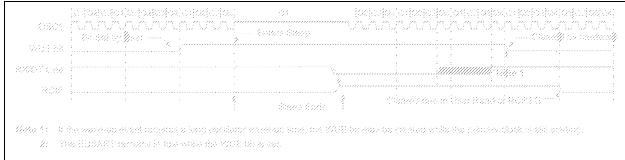
The fact that the WUE bit has been cleared (or is still set) and the RCIF flag is set should not be used as an indicator of the integrity of the data in RCREG. Users should consider implementing a parallel method in firmware to verify received data integrity.

To assure that no actual data is lost, check the RCIDL bit to verify that a receive operation is not in process. If a receive operation is not occurring, the WUE bit may then be set just prior to entering the Sleep mode.

FIGURE 16-7: AUTO-WAKE-UP BIT (WUE) TIMINGS DURING NORMAL OPERATION

0801	YAAAA	pununun	INNUNIA.	13.1	NAMA.	1 N.	A.A.A.	punu	NANANA	191	NA U	1.2 N.E	NAMAN	ununun	320
	1 88.389 by	¥286°				2	2	e e						alip by bas	i den
- 890,483 (ost	4		.2		• • • • • • • • • • • • • • • • • • • •		>	{		· · · · · · · · · · · · · · · · · · ·					
		1	2 2			5 - 2	5	: :				1	ζ.		
XBY Lass -	*	·····	· · · · · · · · · · · · · · · · · · ·	3	UMAAAA	ÛUQ.	ziiiiina			Alth	aaaaaaa	We -		;	
ci ci ce				5 5		2	1. N	5	• ••••••••••••••••••			۰ د میں بی در د			
RCE		·	······································	÷		,		9 •	Acres 6		Sume.	an it	80886	Ç	
	·					1		·	nansearena soa		water ees	toor set	Constraints		

FIGURE 16-8: AUTO-WAKE-UP BIT (WUE) TIMINGS DURING SLEEP



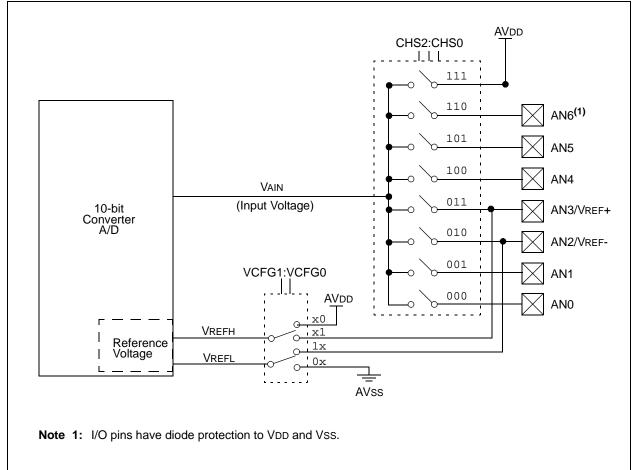
The analog reference voltage is software selectable to either the device's positive and negative supply voltage (AVDD and AVSS), or the voltage level on the RA3/AN3/ VREF+ and RA2/AN2/VREF- pins.

The A/D converter has a unique feature of being able to operate while the device is in Sleep mode. To operate in Sleep, the A/D conversion clock must be derived from the A/D's internal RC oscillator.

The output of the sample and hold is the input into the converter, which generates the result via successive approximation.

A device Reset forces all registers to their Reset state. This forces the A/D module to be turned off and any conversion in progress is aborted.

Each port pin associated with the A/D converter can be configured as an analog input, or as a digital I/O. The ADRESH and ADRESL registers contain the result of the A/D conversion. When the A/D conversion is complete, the result is <u>loaded</u> into the ADRESH/ADRESL registers, the GO/DONE bit (ADCON0 register) is cleared and A/D Interrupt Flag bit, ADIF, is set. The block diagram of the A/D module is shown in Figure 17-1.



19.5.2 DATA EEPROM CODE PROTECTION

The entire data EEPROM is protected from external reads and writes by two bits: CPD and WRTD. CPD inhibits external reads and writes of data EEPROM. WRTD inhibits external writes to data EEPROM. The CPU can continue to read and write data EEPROM, regardless of the protection bit settings.

19.5.3 CONFIGURATION REGISTER PROTECTION

The Configuration registers can be write-protected. The WRTC bit controls protection of the Configuration registers. In normal execution mode, the WRTC bit is readable only. WRTC can only be written via ICSP or an external programmer.

19.6 ID Locations

Eight memory locations (20000h-200007h) are designated as ID locations, where the user can store checksum or other code identification numbers. These locations are both readable and writable during normal execution through the TBLRD and TBLWT instructions, or during program/verify. The ID locations can be read when the device is code-protected.

19.7 In-Circuit Serial Programming

PIC18F1220/1320 microcontrollers can be serially programmed while in the end application circuit. This is simply done with two lines for clock and data and three other lines for power, ground and the programming voltage. This allows customers to manufacture boards with unprogrammed devices and then program the microcontroller just before shipping the product. This also allows the most recent firmware or a custom firmware to be programmed (see Table 19-4).

Note:	The Timer1 oscillator shares the T1OSI and T1OSO pins with the PGD and PGC pins used for programming and debugging.
	When using the Timer1 oscillator, In-Circuit Serial Programming (ICSP) may not function correctly (high voltage or low voltage), or the In-Circuit Debugger (ICD) may not communicate with the controller. As a result of using either ICSP or ICD, the Timer1 crystal may be damaged.
	If ICSP or ICD operations are required, the crystal should be disconnected from the circuit (disconnect either lead), or installed after programming. The oscillator loading capacitors may remain in-circuit during ICSP or ICD operation.

TABLE 19-4: ICSP/ICD CONNECTIONS

Signal	Pin	Notes
PGD	RB7/PGD/T1OSI/ P1D/KBI3	Shared with T1OSC – protect crystal
PGC	RB6/PGC/T1OSO/ T13CKI/P1C/KBI2	Shared with T1OSC – protect crystal
MCLR	MCLR/Vpp/RA5	
Vdd	Vdd	
Vss	Vss	
PGM	RB5/PGM/KBI1	Optional – pull RB5 low is LVP enabled

19.8 In-Circuit Debugger

When the DEBUG bit in Configuration register, CONFIG4L, is programmed to a '0', the In-Circuit Debugger functionality is enabled. This function allows simple debugging functions when used with MPLAB[®] IDE. When the microcontroller has this feature enabled, some resources are not available for general use. Table 19-5 shows which resources are required by the background debugger.

TABLE 19-5: DEBUGGER RESOURCES

I/O pins:	RB6, RB7
Stack:	2 levels
Program Memory:	512 bytes
Data Memory:	10 bytes

To use the In-Circuit Debugger function of the microcontroller, the design must implement In-Circuit Serial Programming connections to MCLR/VPP, VDD, Vss, RB7 and RB6. This will interface to the In-Circuit Debugger module available from Microchip, or one of the third party development tool companies (see the note following **Section 19.7 "In-Circuit Serial Programming"** for more information).

CLRF	Clear f	CLRWDT	Clear Watchdog Timer			
Syntax:	[label]CLRF f[,a]	Syntax:	[label] CLRWDT			
Operands:	$0 \leq f \leq 255$	Operands:	None			
	a ∈ [0,1]	Operation:	000h \rightarrow WDT,			
Operation:	$\begin{array}{l} 000h \rightarrow f \\ 1 \rightarrow Z \end{array}$		$000h \rightarrow WDT$ postscaler, 1 $\rightarrow TO$,			
Status Affected:	Z		$1 \rightarrow \overline{PD}$			
Encoding:		Status Affected:	TO, PD			
Description:	Clears the contents of the specified	Encoding:	0000 0000 0000 0100			
Decemption	register. If 'a' is '0', the Access	Description:	CLRWDT instruction resets the			
	Bank will be selected, overriding		Watchdog Timer. It also resets the			
	the BSR value. If 'a' = 1, then the bank will be selected as per the		postscaler of the WDT. Status bits, TO and PD, are set.			
	BSR value (default).	Words:	1			
Words:	1	Cycles:	1			
Cycles:	1	Q Cycle Activity				
Q Cycle Activity	:	Q1	Q2 Q3 Q4			
Q1	Q2 Q3 Q4	Decode	No Process No			
Decode	Read Process Write register 'f' Data register 'f'		operation Data operation			
		Example:	CLRWDT			
Example:	CLRF FLAG_REG	Before Instru				
Before Instru	uction	WDT Co				
FLAG_R		After Instruc	tion			
After Instruc		WDT Co WDT Po				
FLAG_R	EG = 0x00	TO	= 1			
		PD	= 1			

DAW	Decimal A	djust W Re	gister			
Syntax:	[label] DAW					
Operands:	None	None				
Operation:	(W<3:0>) else	> 9] or [DC + 6 → W<3:0 → W<3:0>;	-			
Status Affected:	(W<7:4>) else	$(W{<}7{:}4{>}) \rightarrow W{<}7{:}4{>};$				
Encoding:	0000	0000 000	0 0111			
Description:	DAW adjus resulting fr two variab format) an packed BC may be se	ests the 8-bit work of the earlied les (each in produces a CD result. The toy DAW regard or to the DAW	value in W, er addition of backed BCD a correct e Carry bit ardless of its			
Words:	1					
Cycles:	1					
Q Cycle Activity:						
Q1	Q2	Q3	Q4			
Decode	Read register W	Process Data	Write W			
Example 1:	DAW					
Before Instru						
W C	= 0xA5 = 0					
DC	= 0					
After Instruct W	ion = 0x05					
C DC	= 1 = 0					
Example 2:	- 0					
Before Instruction						
W	= 0xCE					
C DC	= 0 = 0					
After Instruct	tion					
W C DC	= 0x34 = 1 = 0					

DECF Decrement f						
Syntax:	[label] [[<i>label</i>] DECF f[,d[,a]]				
Operands:	$0 \le f \le 255$ $d \in [0,1]$ $a \in [0,1]$					
Operation: $(f) - 1 \rightarrow dest$						
Status Affecte	d: C, DC, N,	OV, Z				
Encoding:	0000	01da ff	ff ffff			
Description:	the result the result 'f' (default Bank will the BSR v bank will b	It register 'f'. is stored in V is stored bac). If 'a' is '0', be selected, value. If 'a' = be selected a e (default).	V. If 'd' is '1', ck in register the Access overriding 1, then the			
Words:	1	1				
Cycles:	1	1				
Q Cycle Activ	rity:					
Q1	Q2	Q2 Q3				
Decode	e Read register 'f'	Process Data	Write to destination			
Example:		CNT				

 $\begin{array}{rrrr} Before Instruction \\ CNT &=& 0 \\ Z &=& 0 \\ \\ After Instruction \\ CNT &=& 0 \\ Z &=& 1 \end{array}$

INCFSZ	Increment	t f, skip if 0				
Syntax:	[label]	NCFSZ f[,d [,a]]			
Operands:	0 ≤ f ≤ 255 d ∈ [0,1] a ∈ [0,1]	5				
Operation:	(f) + 1 \rightarrow c skip if resu					
Status Affected:	None					
Encoding:	0011	11da ffi	f ffff			
Description:	The contents of register 'f' are incremented. If 'd' is '0', the result is placed in W. If 'd' is '1', the result is placed back in register 'f' (default). If the result is '0', the next instruc- tion, which is already fetched, is discarded and a NOP is executed instead, making it a 2-cycle instruc- tion. If 'a' is '0', the Access Bank will be selected, overriding the BSR value. If 'a' = 1, then the bank will be selected as per the BSR value					
Manda.	(default).	(derault).				
Words: Cycles:	1 1(2)					
Note: 3 cycles if skip and follow by a 2-word instruction. Q Cycle Activity:						
Q1	Q2	Q3	Q4			
Decode	Read register 'f'	Process Data	Write to destination			
If skip:		Dulu	destination			
Q1	Q2	Q3	Q4			
No	No	No	No			
operation If skip and follow	operation	operation	operation			
Q1	Q2	Q3	Q4			
No	No	No	No			
operation	operation	operation	operation			
No	No	No	No			
operation	operation	operation	operation			
Example:	HERE I NZERO : ZERO :		Т			
Before Instru	iction					
PC	= Address	(HERE)				
After Instruction						
CNT If CNT	= CNT + 1 = 0;	I				
PC If CNT		(ZERO)				
PC		(NZERO)				

	lest, lt ≠ 0 10da nts of re ed. If 'd' n W. If 'c pack in r lt is not , which discarc nstead, uction. I ank will b 3SR val <i>i</i> ll be se e (defau	ffff egister ' is '0', t d' is '1', register '0', the is alrea led and making f 'a' is ' be sele ue. If 'a elected lt). skip an d instru	ffff f' are the result the result the result tf' next ady d a NOP is g it a 2- 0', the cted, ove as per th ad followe
$d \in [0,1]$ $a \in [0,1]$ $f) + 1 \rightarrow c$ skip if resuves the second	lest, $11 \neq 0$ 10da ints of re ed. If 'd' in W. If 'd' oack in r discarc nstead, uction. I ink will B 3SR val <i>i</i> defau ycles if a 2-wor Q3	egister ' is '0', t d' is '1', register '0', the is alrea led and making f 'a' is ' be sele ue. If 'a elected lt). skip an d instru	f' are the result the
Skip if resu None 0100 The conte ncrements s placed is s placed is default). f the resu nstruction etched, is executed i cycle instr Access Ba iding the I he bank v 3SR value (2) Note: 3 c by Q2 Read	ult \neq 0 10da nts of re ed. If 'd' n W. If 'o pack in r lt is not , which discarc nstead, uction. I ank will I BSR val vill be se e (defau ycles if a 2-wor Q3	egister ' is '0', t d' is '1', register '0', the is alrea led and making f 'a' is ' be sele ue. If 'a elected lt). skip an d instru	f' are the result the
0100 The contents s placed is s placed is s placed is s placed is default). f the resund nstruction etched, is executed in cycle instr Access Basiliani the bank was SR value (2) Note: 3 co by Q2 Read	Ints of re ed. If 'd' n W. If 'd' pack in r lt is not , which discarc nstead, uction. I ank will I BSR val vill be se e (defau ycles if a 2-wor	egister ' is '0', t d' is '1', register '0', the is alrea led and making f 'a' is ' be sele ue. If 'a elected lt). skip an d instru	f' are the result the
The contencrements s placed in s placed in s placed in s placed in default). f the resunstruction etched, is executed in cycle instr Access Ba iding the I he bank w BSR value (2) Note: 3 c by Q2 Read	Ints of re ed. If 'd' n W. If 'd' pack in r lt is not , which discarc nstead, uction. I ank will I BSR val vill be se e (defau ycles if a 2-wor	egister ' is '0', t d' is '1', register '0', the is alrea led and making f 'a' is ' be sele ue. If 'a elected lt). skip an d instru	f' are the result the
ncrements s placed is s placed b default). f the resunstruction etched, is executed i cycle instr Access Ba iding the I he bank w 3SR value (2) Note: 3 c by Q2 Read	ed. If 'd' n W. If 'd pack in r lt is not discarc nstead, uction. I ank will I BSR val <i>i</i> ll be se (defau ycles if a 2-wor	is '0', t d' is '1', egister '0', the is alrea led anc making f 'a' is ' be sele ue. If 'a elected lt).	the result the result off next ady d a NOP is g it a 2- 0', the cted, ove i' = 1, the as per th ad followe
Q2 Read	Q3		
Read			Q4
Read			(J4
	Data	ess	Write to destination
	Dat	u (
Q2	Q3	6	Q4
No	No		No
peration by 2-wore	operat operation		operation
Q2	-		Q4
No	No		No
			operation
			No operation
ZERO	INFSNZ	REG	
	6 (HERE)	
REG + 1 0;		0)	
	No pperation No pperation LERE ZERO VZERO DN Address REG + 7 0;	No No operation operation No No operation operation indextream operation indextream INFSNZ ZERO VZERO VZERO On Address (HERE REG + 1 0; Address (NZER)	No No operation operation No No operation operation

NEGF	Negate f					
Syntax:	[label]	NEGF	f [,a]			
Operands:	0 ≤ f ≤ 255 a ∈ [0,1]	$\begin{array}{l} 0 \leq f \leq 255 \\ a \in [0,1] \end{array}$				
Operation:	$(\overline{f}) + 1 \rightarrow f$:				
Status Affected:	N, OV, C,	DC, Z				
Encoding:	0110	110a	ffff	ffff		
Description: Location 'f' is negated using two's complement. The result is placed in the data memory location 'f'. If 'a' is '0', the Access Bank will be selected, overriding the BSR value. If 'a' = 1, then the bank will be selected as per the BSR value.						
Words:	1					
Cycles:	1					
Q Cycle Activity:						
Q1	Q2	Q	3	Q4		
Decode	Read register 'f'	Proce Dat		Write gister 'f'		
Example: NEGF REG, 1						
Before Instruction REG = 0011 1010 [0x3A]						

NOF)	No Opera	ation				
Synt	ax:	[label]	[label] NOP				
Ope	rands:	None	None				
Operation:		No opera	tion				
Statu	us Affected:	None					
Encoding:		0000	0000	000	0	0000	
		1111	xxxx	XXX	x	XXXX	
Des	cription:	No opera	No operation.				
Wor	ds:	1					
Cycl	es:	1					
QC	ycle Activity:						
Q1		Q2	Q3		Q4		
	Decode	No	No			No	
		operation	operation		op	operation	

Example:

None.

After Instruction

REG = 1100 0110 [0xC6]

22.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings^(†)

Ambient temperature under bias	40°C to +125°C
Storage temperature	65°C to +150°C
Voltage on any pin with respect to Vss (except VDD, MCLR and RA4)	0.3V to (VDD + 0.3V)
Voltage on VDD with respect to Vss	0.3V to +5.5V
Voltage on MCLR with respect to Vss (Note 2)	0V to +13.25V
Voltage on RA4 with respect to Vss	0V to +8.5V
Total power dissipation (Note 1)	1.0W
Maximum current out of Vss pin	
Maximum current into VDD pin	250 mA
Input clamp current, Iк (Vi < 0 or Vi > VDD)	±20 mA
Output clamp current, loк (Vo < 0 or Vo > VDD)	±20 mA
Maximum output current sunk by any I/O pin	25 mA
Maximum output current sourced by any I/O pin	25 mA
Maximum current sunk by all ports	200 mA
Maximum current sourced by all ports	200 mA
Note 1: Power dissipation is calculated as follows:	

- Pdis = VDD x {IDD $-\Sigma$ IOH} + Σ {(VDD VOH) x IOH} + Σ (VOL x IOL)
- **2:** Voltage spikes below Vss at the MCLR/VPP pin, inducing currents greater than 80 mA, may cause latch-up. Thus, a series resistor of 50-100Ω should be used when applying a "low" level to the MCLR/VPP pin, rather than pulling this pin directly to Vss.

† NOTICE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

TABLE 22-2: LOW-VOLTAGE DETECT CHARACTERISTICS (CONTINUED)

PIC18LF1220/1320 (Industrial) PIC18F1220/1320 (Industrial, Extended)			$\label{eq:standard Operating Conditions (unless otherwise stated)} Operating temperature -40°C \leq TA \leq +85°C for industrial \\ \begin{tabular}{lllllllllllllllllllllllllllllllllll$,	
							Param No.	Symbol
D420F		LVD Voltage on VDD	Industria	al Low Vol	tage (-40	°C to -10°	°C)	
		PIC18LF1220/1320	LVDL<3:0> = 0000	N/A	N/A	N/A	V	Reserved
			LVDL<3:0> = 0001	N/A	N/A	N/A	V	Reserved
			LVDL<3:0> = 0010	1.99	2.26	2.53	V	
			LVDL<3:0> = 0011	2.16	2.45	2.75	V	
			LVDL<3:0> = 0100	2.25	2.55	2.86	V	
			LVDL<3:0> = 0101	2.43	2.77	3.10	V	
			LVDL<3:0> = 0110	2.53	2.87	3.21	V	
			LVDL<3:0> = 0111	2.70	3.07	3.43	V	
			LVDL<3:0> = 1000	2.96	3.36	3.77	V	
			LVDL<3:0> = 1001	3.14	3.57	4.00	V	
			LVDL<3:0> = 1010	3.23	3.67	4.11	V	
			LVDL<3:0> = 1011	3.41	3.87	4.34	V	
			LVDL<3:0> = 1100	3.58	4.07	4.56	V	
			LVDL<3:0> = 1101	3.76	4.28	4.79	V	
			LVDL<3:0> = 1110	4.04	4.60	5.15	V	
		LVD Voltage on VDD	Fransition High-to-Low	w Industrial (-10°C to +85°C)			-	
D420G		PIC18F1220/1320	LVDL<3:0> = 1101	3.93	4.28	4.62	V	
			LVDL<3:0> = 1110	4.23	4.60	4.96	V	
		LVD Voltage on VDD	Fransition High-to-Low	Industria	al (-40°C t	o -10°C)		
D420H		PIC18F1220/1320	LVDL<3:0> = 1101	3.76	4.28	4.79	V	
			LVDL<3:0> = 1110	4.04	4.60	5.15	V	
LVD Voltage on VDD Transition High-to-Low Extended		d (-10°C t	to +85°C)				
D420J		PIC18F1220/1320	LVDL<3:0> = 1101	3.94	4.28	4.62	V	
			LVDL<3:0> = 1110	4.23	4.60	4.96	V	
		LVD Voltage on VDD	Fransition High-to-Low	Extende	d (-40°C 1	to -10°C,	+85°C to	+125°C)
D420K		PIC18F1220/1320	LVDL<3:0> = 1101	3.77	4.28	4.79	V	
			LVDL<3:0> = 1110	4.05	4.60	5.15	V	

Legend: Shading of rows is to assist in readability of the table.

† Production tested at TAMB = 25°C. Specifications over temperature limits ensured by characterization.

22.4 AC (Timing) Characteristics

22.4.1 TIMING PARAMETER SYMBOLOGY

The timing parameter symbols have been created following one of the following formats:

1. TppS2ppS	3	3. Tcc:st	(I ² C specifications only)
2. TppS		4. Ts	(I ² C specifications only)
Т			
F	Frequency	Т	Time
Lowercase le	etters (pp) and their meanings:		
рр			
сс	CCP1	osc	OSC1
ck	CLKO	rd	RD
cs	CS	rw	RD or WR
di	SDI	sc	SCK
do	SDO	SS	SS
dt	Data in	tO	TOCKI
io	I/O port	t1	T13CKI
mc	MCLR	wr	WR
Uppercase le	etters and their meanings:		
S			
F	Fall	Р	Period
н	High	R	Rise
I	Invalid (High-Impedance)	V	Valid
L	Low	Z	High-Impedance
I ² C only			
AA	output access	High	High
BUF	Bus free	Low	Low
TCC:ST (I ² C s	specifications only)		
CC			
HD	Hold	SU	Setup
ST			
DAT	DATA input hold	STO	Stop condition
STA	Start condition		

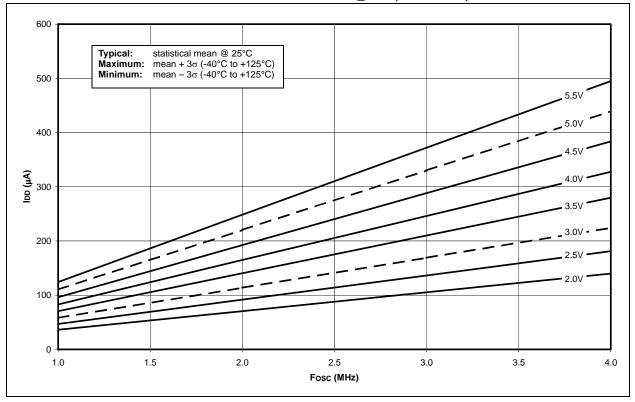


FIGURE 23-11: TYPICAL IDD vs. Fosc OVER VDD PRI_IDLE, EC MODE, +25°C



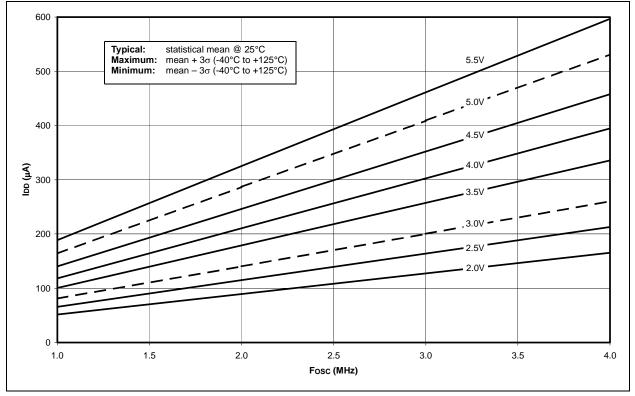
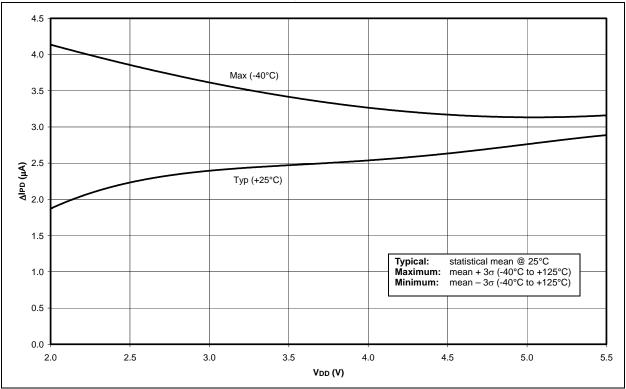
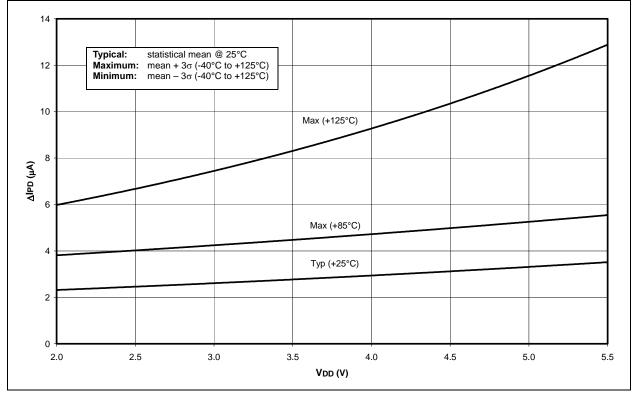


FIGURE 23-29: △IPD FSCM vs. VDD OVER TEMPERATURE PRI_IDLE MODE, EC OSCILLATOR AT 32 kHz, -40°C TO +125°C







APPENDIX A: REVISION HISTORY

Revision A (August 2002)

Original data sheet for PIC18F1220/1320 devices.

Revision B (November 2002)

This revision includes significant changes to Section 2.0, Section 3.0 and Section 19.0, as well as updates to the Electrical Specifications in Section 22.0 and includes minor corrections to the data sheet text.

Revision C (May 2004)

This revision includes updates to the Electrical Specifications in **Section 22.0**, the DC and AC Characteristics Graphs and Tables in **Section 23.0** and includes minor corrections to the data sheet text.

Revision D (October 2006)

This revision includes updates to the packaging diagrams.

Revision E (January 2007)

This revision includes updates to the packaging diagrams.

Revision F (February 2007)

This revision includes updates to the packaging diagrams.

TABLE B-1: DEVICE DIFFERENCES

Features	PIC18F1220	PIC18F1320
Program Memory (Bytes)	4096	8192
Program Memory (Instructions)	2048	4096
Interrupt Sources	15	15
I/O Ports	Ports A, B	Ports A, B
Enhanced Capture/Compare/PWM Modules	1	1
10-bit Analog-to-Digital Module	7 input channels	7 input channels
Packages	18-pin SDIP 18-pin SOIC 20-pin SSOP 28-pin QFN	18-pin SDIP 18-pin SOIC 20-pin SSOP 28-pin QFN

Revision G (April 2015)

Added Section 22.5: High Temperature Operation in the Electrical Specifications section.

APPENDIX B: DEVICE DIFFERENCES

The differences between the devices listed in this data sheet are shown in Table B-1.

Worldwide Sales and Service

AMERICAS

Corporate Office 2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200 Fax: 480-792-7277 Technical Support: http://www.microchip.com/ support Web Address: www.microchip.com

Atlanta Duluth, GA Tel: 678-957-9614 Fax: 678-957-1455

Austin, TX Tel: 512-257-3370

Boston Westborough, MA Tel: 774-760-0087 Fax: 774-760-0088

Chicago Itasca, IL Tel: 630-285-0071 Fax: 630-285-0075

Cleveland Independence, OH Tel: 216-447-0464 Fax: 216-447-0643

Dallas Addison, TX Tel: 972-818-7423 Fax: 972-818-2924

Detroit Novi, MI Tel: 248-848-4000

Houston, TX Tel: 281-894-5983 Indianapolis

Noblesville, IN Tel: 317-773-8323 Fax: 317-773-5453

Los Angeles Mission Viejo, CA Tel: 949-462-9523 Fax: 949-462-9608

New York, NY Tel: 631-435-6000

San Jose, CA Tel: 408-735-9110

Canada - Toronto Tel: 905-673-0699 Fax: 905-673-6509

ASIA/PACIFIC

Asia Pacific Office Suites 3707-14, 37th Floor Tower 6, The Gateway Harbour City, Kowloon

Hong Kong Tel: 852-2943-5100 Fax: 852-2401-3431

Australia - Sydney Tel: 61-2-9868-6733 Fax: 61-2-9868-6755

China - Beijing Tel: 86-10-8569-7000 Fax: 86-10-8528-2104

China - Chengdu Tel: 86-28-8665-5511 Fax: 86-28-8665-7889

China - Chongqing Tel: 86-23-8980-9588 Fax: 86-23-8980-9500

China - Dongguan Tel: 86-769-8702-9880

China - Hangzhou Tel: 86-571-8792-8115 Fax: 86-571-8792-8116

China - Hong Kong SAR Tel: 852-2943-5100 Fax: 852-2401-3431

China - Nanjing Tel: 86-25-8473-2460 Fax: 86-25-8473-2470

China - Qingdao Tel: 86-532-8502-7355 Fax: 86-532-8502-7205

China - Shanghai Tel: 86-21-5407-5533 Fax: 86-21-5407-5066

China - Shenyang Tel: 86-24-2334-2829 Fax: 86-24-2334-2393

China - Shenzhen Tel: 86-755-8864-2200 Fax: 86-755-8203-1760

China - Wuhan Tel: 86-27-5980-5300 Fax: 86-27-5980-5118

China - Xian Tel: 86-29-8833-7252 Fax: 86-29-8833-7256

ASIA/PACIFIC

China - Xiamen Tel: 86-592-2388138 Fax: 86-592-2388130

China - Zhuhai Tel: 86-756-3210040 Fax: 86-756-3210049

India - Bangalore Tel: 91-80-3090-4444 Fax: 91-80-3090-4123

India - New Delhi Tel: 91-11-4160-8631 Fax: 91-11-4160-8632

India - Pune Tel: 91-20-3019-1500

Japan - Osaka Tel: 81-6-6152-7160 Fax: 81-6-6152-9310

Japan - Tokyo Tel: 81-3-6880- 3770 Fax: 81-3-6880-3771

Korea - Daegu Tel: 82-53-744-4301 Fax: 82-53-744-4302

Korea - Seoul Tel: 82-2-554-7200 Fax: 82-2-558-5932 or 82-2-558-5934

Malaysia - Kuala Lumpur Tel: 60-3-6201-9857 Fax: 60-3-6201-9859

Malaysia - Penang Tel: 60-4-227-8870 Fax: 60-4-227-4068

Philippines - Manila Tel: 63-2-634-9065 Fax: 63-2-634-9069

Singapore Tel: 65-6334-8870 Fax: 65-6334-8850

Taiwan - Hsin Chu Tel: 886-3-5778-366 Fax: 886-3-5770-955

Taiwan - Kaohsiung Tel: 886-7-213-7828

Taiwan - Taipei Tel: 886-2-2508-8600 Fax: 886-2-2508-0102

Thailand - Bangkok Tel: 66-2-694-1351 Fax: 66-2-694-1350

EUROPE

Austria - Wels Tel: 43-7242-2244-39 Fax: 43-7242-2244-393

Denmark - Copenhagen Tel: 45-4450-2828 Fax: 45-4485-2829

France - Paris Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

Germany - Dusseldorf Tel: 49-2129-3766400

Germany - Munich Tel: 49-89-627-144-0 Fax: 49-89-627-144-44

Germany - Pforzheim Tel: 49-7231-424750

Italy - Milan Tel: 39-0331-742611 Fax: 39-0331-466781

Italy - Venice Tel: 39-049-7625286

Netherlands - Drunen Tel: 31-416-690399 Fax: 31-416-690340

Poland - Warsaw Tel: 48-22-3325737

Spain - Madrid Tel: 34-91-708-08-90 Fax: 34-91-708-08-91

Sweden - Stockholm Tel: 46-8-5090-4654

UK - Wokingham Tel: 44-118-921-5800 Fax: 44-118-921-5820

01/27/15